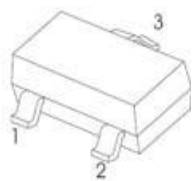
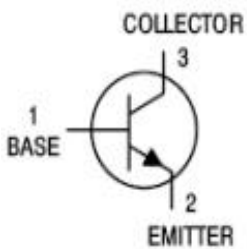


TRANSISTOR (NPN)	SOT-23 Plastic-Encapsulate Transistors																																				
<p><u>SOT-23</u></p>   <p>1.BASE 2.EMITTER 3.COLLECTOR</p> <p>Marking :CR</p>	<p>Features</p> <ul style="list-style-type: none"> ※ Complimentary to 2SA733 ※ Excellent HFE Linearity ※ LOW noise 																																				
<p>MAXIMUM RATINGS (Ta=25°C unless otherwise noted)</p> <table border="1"> <thead> <tr> <th>Parameter</th> <th>Symbol</th> <th>Value</th> <th>Unit</th> </tr> </thead> <tbody> <tr> <td>Collector-Base Voltage</td> <td>V_{CB0}</td> <td>60</td> <td>V</td> </tr> <tr> <td>Collector-Emitter Voltage</td> <td>V_{CE0}</td> <td>50</td> <td>V</td> </tr> <tr> <td>Emitter-Base Voltage</td> <td>V_{EB0}</td> <td>5</td> <td>V</td> </tr> <tr> <td>Collector Current</td> <td>I_C</td> <td>150</td> <td>mA</td> </tr> <tr> <td>Collector Power Dissipation</td> <td>P_C</td> <td>200</td> <td>mW</td> </tr> <tr> <td>Thermal Resistance From Junction To Ambient</td> <td>R_{θJA}</td> <td>417</td> <td>°C/W</td> </tr> <tr> <td>Junction Temperature</td> <td>T_j</td> <td>150</td> <td>°C</td> </tr> <tr> <td>Storage Temperature</td> <td>T_{stg}</td> <td>-55~+150</td> <td>°C</td> </tr> </tbody> </table>		Parameter	Symbol	Value	Unit	Collector-Base Voltage	V _{CB0}	60	V	Collector-Emitter Voltage	V _{CE0}	50	V	Emitter-Base Voltage	V _{EB0}	5	V	Collector Current	I _C	150	mA	Collector Power Dissipation	P _C	200	mW	Thermal Resistance From Junction To Ambient	R _{θJA}	417	°C/W	Junction Temperature	T _j	150	°C	Storage Temperature	T _{stg}	-55~+150	°C
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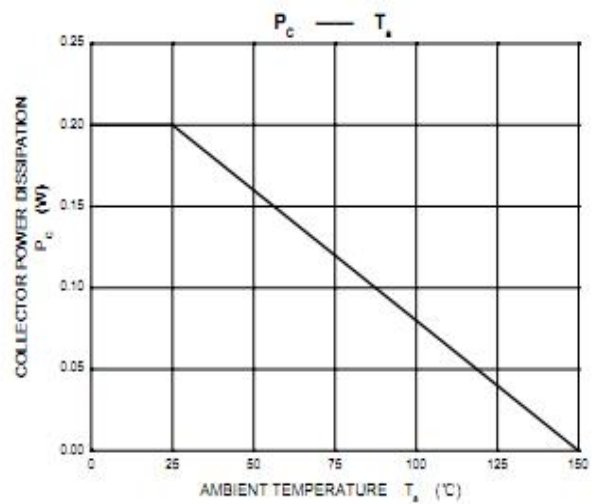
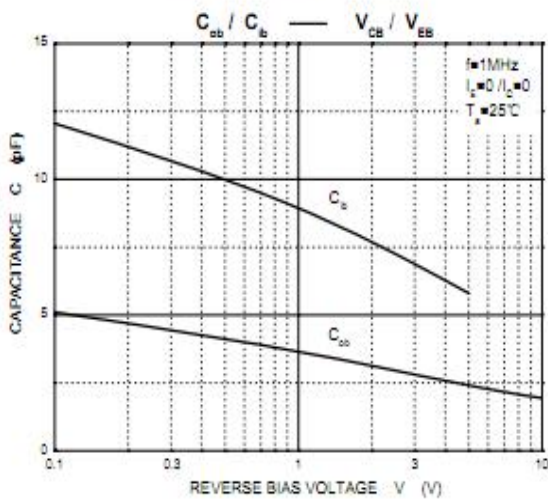
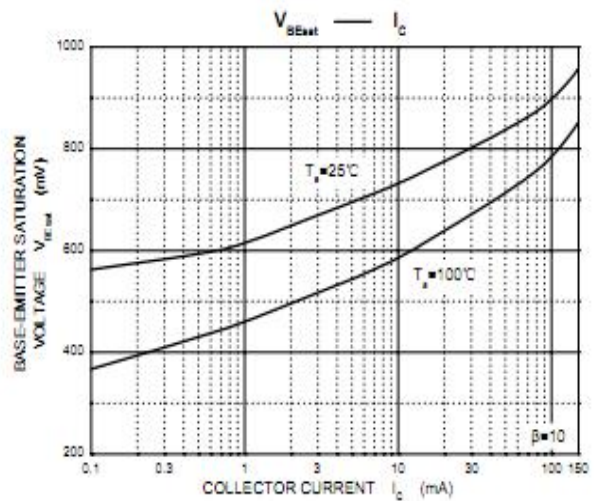
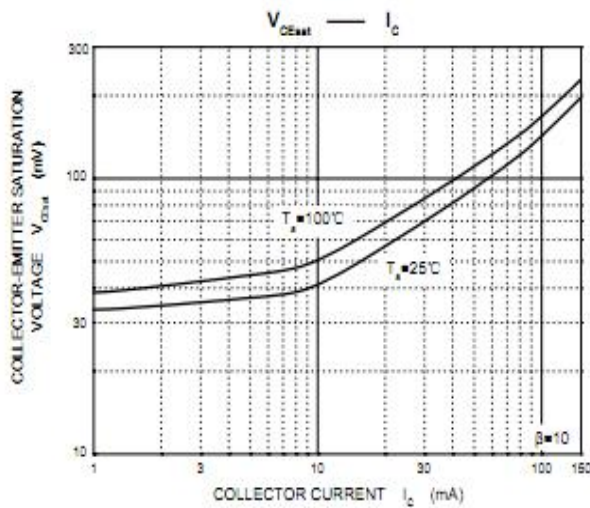
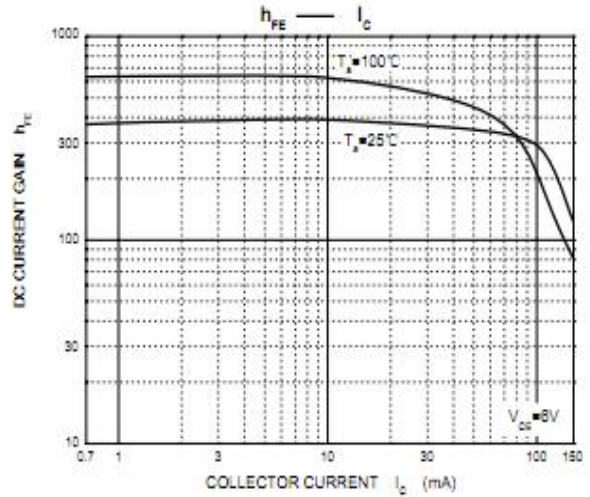
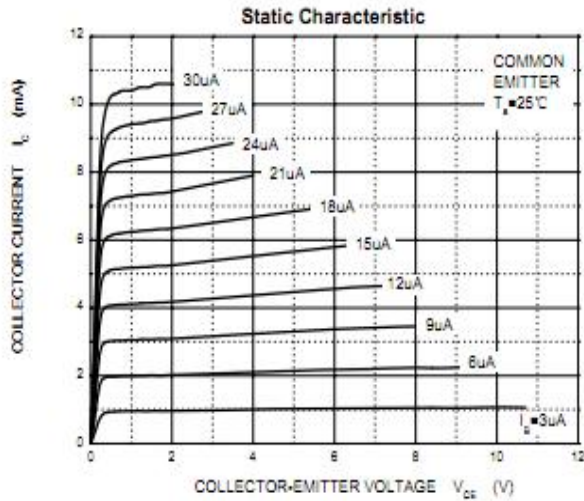
ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC= 100 μA, IE=0	60			V
Collector-emitter breakdown voltage	V(BR)CEO	IC= 1mA, IB=0	50			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100 μA, IC=0	5			V
Collector cut-off current	ICBO	VCB=60 V, IE=0			0.1	μA
Collector cut-off current	ICER	VCB=55V, R=10MΩ			0.1	μA
Emitter cut-off current	IEBO	VEB= 5V, IC=0			0.1	μA
DC current gain	hFE	VCE=6V, IC= 1mA	120		400	
	hFE	VCE=6V, IC= 0.1mA	40			
Collector-emitter saturation voltage	VCE(sat)	IC=100 mA, IB= 10mA			0.3	V
Base-emitter saturation voltage	VBE(sat)	IC=100 mA, IB= 10mA			1	V
Transition frequency	fT	VCE=6V, IC= 10mA f=30MHz	150			MHz
Collector Output Capacitance	Cob	VCE=10V, IE= 0 f=1MHz			3.0	pf
Noise Figure	NF	VCE=6V, IC= 20mA Rg=10kΩ; f=30MHz		4	10	dB

CLASSIFICATION OF hFI

Rank	L	H	
Range	130-200	200-400	

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



单击下面可查看定价，库存，交付和生命周期等信息

[>>DIOS\(迪恩思\)](#)